



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Features

- Incorporates the ARM7TDMI® ARM® Thumb® Processor
 - High-performance 32-bit RISC Architecture
 - High-density 16-bit Instruction Set
 - Leader in MIPS/Watt
 - EmbeddedICE™ In-circuit Emulation, Debug Communication Channel Support
- Internal High-speed Flash
 - 512 Kbytes, Organized in Two Contiguous Banks of 1024 Pages of 256 Bytes Dual Plane (SAM7SE512)
 - 256 Kbytes (SAM7SE256) Organized in One Bank of 1024 Pages of 256 Bytes Single Plane (SAM7SE256)
 - 32 Kbytes (SAM7SE32) Organized in One Bank of 256 Pages of 128 Bytes Single Plane (SAM7SE32)
 - Single Cycle Access at Up to 30 MHz in Worst Case Conditions
 - Prefetch Buffer Optimizing Thumb Instruction Execution at Maximum Speed
 - Page Programming Time: 6 ms, Including Page Auto-erase, Full Erase Time: 15 ms
 - 10,000 Erase Cycles, 10-year Data Retention Capability, Sector Lock Capabilities, Flash Security Bit
 - Fast Flash Programming Interface for High Volume Production
- 32 Kbytes (SAM7SE512/256) or 8 Kbytes (SAM7SE32) of Internal High-speed SRAM, Single-cycle Access at Maximum Speed
- One External Bus Interface (EBI)
 - Supports SDRAM, Static Memory, Glueless Connection to CompactFlash® and ECC-enabled NAND Flash
- Memory Controller (MC)
 - Embedded Flash Controller
 - Memory Protection Unit
 - Abort Status and Misalignment Detection
- Reset Controller (RSTC)
 - Based on Power-on Reset Cells and Low-power Factory-calibrated Brownout Detector
 - Provides External Reset Signal Shaping and Reset Source Status
- Clock Generator (CKGR)
 - Low-power RC Oscillator, 3 to 20 MHz On-chip Oscillator and One PLL
- Power Management Controller (PMC)
 - Power Optimization Capabilities, Including Slow Clock Mode (Down to 500 Hz) and Idle Mode
 - Three Programmable External Clock Signals
- Advanced Interrupt Controller (AIC)
 - Individually Maskable, Eight-level Priority, Vectored Interrupt Sources
 - Two External Interrupt Sources and One Fast Interrupt Source, Spurious Interrupt Protected
- Debug Unit (DBGU)
 - Two-wire UART and Support for Debug Communication Channel interrupt, Programmable ICE Access Prevention
 - Mode for General Purpose Two-wire UART Serial Communication
- Periodic Interval Timer (PIT)
 - 20-bit Programmable Counter plus 12-bit Interval Counter
- Windowed Watchdog (WDT)
 - 12-bit key-protected Programmable Counter



AT91SAM ARM-based Flash MCU

SAM7SE512
SAM7SE256
SAM7SE32

Summary

NOTE: This is a summary document.
The complete document is available on
the Atmel website at www.atmel.com.

6222GS-ATARM-6-Sep-11



- Provides Reset or Interrupt Signals to the System
- Counter May Be Stopped While the Processor is in Debug State or in Idle Mode
- Real-time Timer (RTT)
 - 32-bit Free-running Counter with Alarm
 - Runs Off the Internal RC Oscillator
- Three Parallel Input/Output Controllers (PIO)
 - Eighty-eight Programmable I/O Lines Multiplexed with up to Two Peripheral I/Os
 - Input Change Interrupt Capability on Each I/O Line
 - Individually Programmable Open-drain, Pull-up Resistor and Synchronous Output
 - Schmitt Trigger on All inputs
- Eleven Peripheral DMA Controller (PDC) Channels
- One USB 2.0 Full Speed (12 Mbits per second) Device Port
 - On-chip Transceiver, Eight Endpoints, 2688-byte Configurable Integrated FIFOs
- One Synchronous Serial Controller (SSC)
 - Independent Clock and Frame Sync Signals for Each Receiver and Transmitter
 - I²S Analog Interface Support, Time Division Multiplex Support
 - High-speed Continuous Data Stream Capabilities with 32-bit Data Transfer
- Two Universal Synchronous/Asynchronous Receiver Transmitters (USART)
 - Individual Baud Rate Generator, IrDA[®] Infrared Modulation/Demodulation
 - Support for ISO7816 T0/T1 Smart Card, Hardware Handshaking, RS485 Support
 - Full Modem Line Support on USART1
- One Master/Slave Serial Peripheral Interfaces (SPI)
 - 8- to 16-bit Programmable Data Length, Four External Peripheral Chip Selects
- One Three-channel 16-bit Timer/Counter (TC)
 - Three External Clock Inputs, Two Multi-purpose I/O Pins per Channel
 - Double PWM Generation, Capture/Waveform Mode, Up/Down Capability
- One Four-channel 16-bit PWM Controller (PWMC)
- One Two-wire Interface (TWI)
 - Master, Multi-Master and Slave Mode Support, All Two-wire Atmel EEPROMs Supported
 - General Call Supported in Slave Mode
- One 8-channel 10-bit Analog-to-Digital Converter, Four Channels Multiplexed with Digital I/Os
- SAM-BA[®]
 - Default Boot program
 - Interface with SAM-BA Graphic User Interface
- IEEE[®] 1149.1 JTAG Boundary Scan on All Digital Pins
- Four High-current Drive I/O lines, Up to 16 mA Each
- Power Supplies
 - Embedded 1.8V Regulator, Drawing up to 100 mA for the Core and External Components
 - 1.8V or 3.3V VDDIO I/O Lines Power Supply, Independent 3.3V VDDFLASH Flash Power Supply
 - 1.8V VDDCORE Core Power Supply with Brownout Detector
- Fully Static Operation:
 - Up to 55 MHz at 1.8V and 85° C Worst Case Conditions
 - Up to 48 MHz at 1.65V and 85° C Worst Case Conditions
- Available in a 128-lead LQFP Green Package, or a 144-ball LFBGA RoHS-compliant Package

1. Description

Atmel's SAM7SE Series is a member of its Smart ARM Microcontroller family based on the 32-bit ARM7™ RISC processor and high-speed Flash memory.

- SAM7SE512 features a 512-Kbyte high-speed Flash and a 32 Kbyte SRAM.
- SAM7SE256 features a 256-Kbyte high-speed Flash and a 32 Kbyte SRAM.
- SAM7SE32 features a 32-Kbyte high-speed Flash and an 8 Kbyte SRAM.

It also embeds a large set of peripherals, including a USB 2.0 device, an External Bus Interface (EBI), and a complete set of system functions minimizing the number of external components.

The EBI incorporates controllers for synchronous DRAM (SDRAM) and Static memories and features specific circuitry facilitating the interface for NAND Flash, SmartMedia and CompactFlash.

The device is an ideal migration path for 8/16-bit microcontroller users looking for additional performance, extended memory and higher levels of system integration.

The embedded Flash memory can be programmed in-system via the JTAG-ICE interface or via a parallel interface on a production programmer prior to mounting. Built-in lock bits and a security bit protect the firmware from accidental overwrite and preserve its confidentiality.

The SAM7SE Series system controller includes a reset controller capable of managing the power-on sequence of the microcontroller and the complete system. Correct device operation can be monitored by a built-in brownout detector and a watchdog running off an integrated RC oscillator.

By combining the ARM7TDMI processor with on-chip Flash and SRAM, and a wide range of peripheral functions, including USART, SPI, External Bus Interface, Timer Counter, RTT and Analog-to-Digital Converters on a monolithic chip, the SAM7SE512/256/32 is a powerful device that provides a flexible, cost-effective solution to many embedded control applications.

1.1 Configuration Summary of the SAM7SE512, SAM7SE256 and SAM7SE32

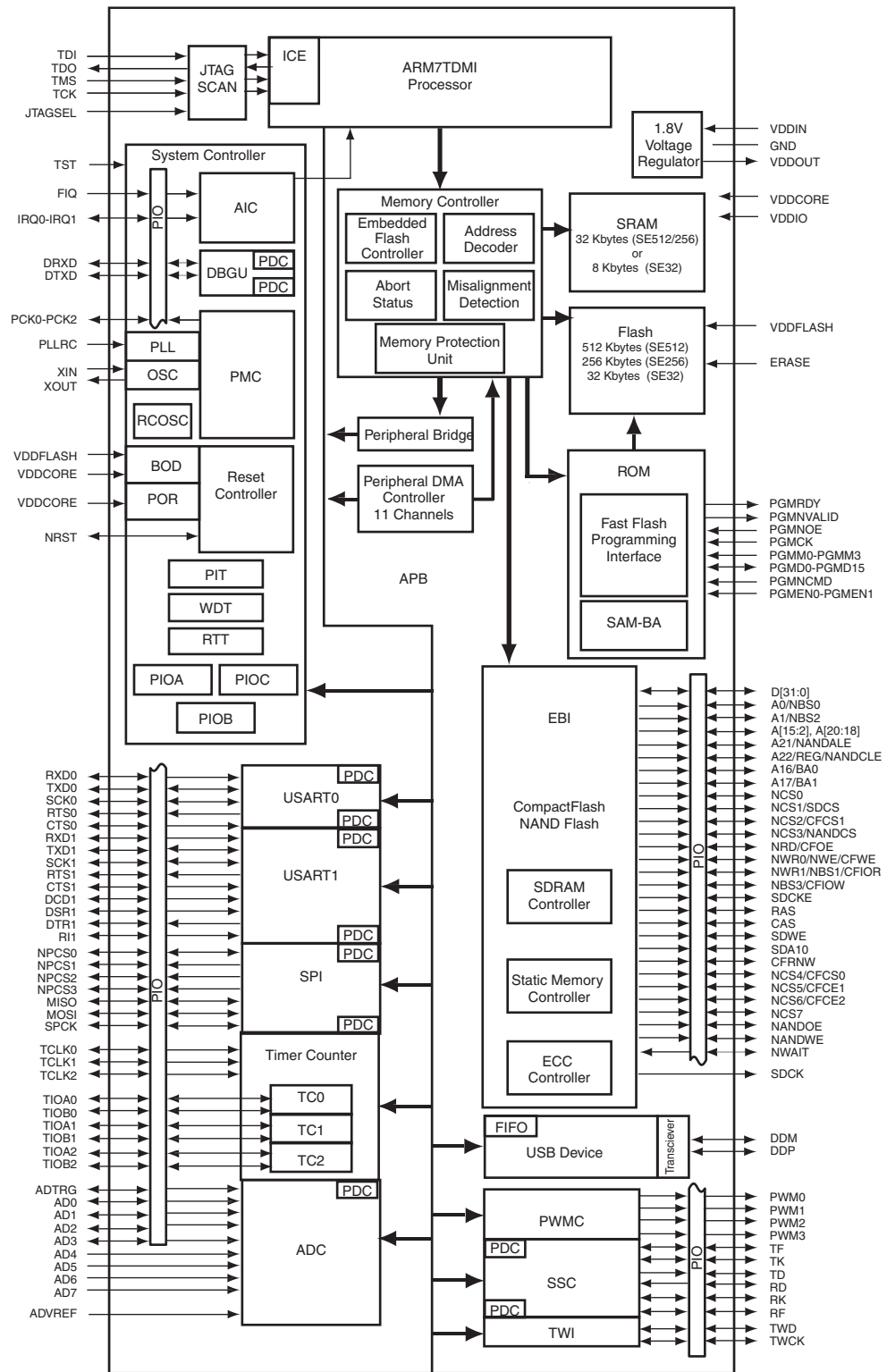
The SAM7SE512, SAM7SE256 and SAM7SE32 differ in memory sizes and organization. [Table 1-1](#) below summarizes the configurations for the three devices.

Table 1-1. Configuration Summary

Device	Flash Size	Flash Organization	RAM Size
SAM7SE512	512K bytes	dual plane	32K bytes
SAM7SE256	256K bytes	single plane	32K bytes
SAM7SE32	32K bytes	single plane	8K bytes

2. Block Diagram

Figure 2-1. SAM7SE512/256/32 Block Diagram Signal Description



3. Signal Description

Table 3-1. Signal Description List

Signal Name	Function	Type	Active Level	Comments
Power				
VDDIN	Voltage Regulator and ADC Power Supply Input	Power		3V to 3.6V
VDDOUT	Voltage Regulator Output	Power		1.85V
VDDFLASH	Flash and USB Power Supply	Power		3V to 3.6V
VDDIO	I/O Lines Power Supply	Power		3V to 3.6V or 1.65V to 1.95V
VDDCORE	Core Power Supply	Power		1.65V to 1.95V
VDDPLL	PLL	Power		1.65V to 1.95V
GND	Ground	Ground		
Clocks, Oscillators and PLLs				
XIN	Main Oscillator Input	Input		
XOUT	Main Oscillator Output	Output		
PLLRC	PLL Filter	Input		
PCK0 - PCK2	Programmable Clock Output	Output		
ICE and JTAG				
TCK	Test Clock	Input		No pull-up resistor
TDI	Test Data In	Input		No pull-up resistor
TDO	Test Data Out	Output		
TMS	Test Mode Select	Input		No pull-up resistor.
JTAGSEL	JTAG Selection	Input		Pull-down resistor ⁽¹⁾
Flash Memory				
ERASE	Flash and NVM Configuration Bits Erase Command	Input	High	Pull-down resistor ⁽¹⁾
Reset/Test				
NRST	Microcontroller Reset	I/O	Low	Open drain with pull-up resistor ⁽¹⁾
TST	Test Mode Select	Input	High	Pull-down resistor ⁽¹⁾
Debug Unit				
DRXD	Debug Receive Data	Input		
DTXD	Debug Transmit Data	Output		
AIC				
IRQ0 - IRQ1	External Interrupt Inputs	Input		
FIQ	Fast Interrupt Input	Input		



Table 3-1. Signal Description List (Continued)

Signal Name	Function	Type	Active Level	Comments
PIO				
PA0 - PA31	Parallel IO Controller A	I/O		Pulled-up input at reset
PB0 - PB31	Parallel IO Controller B	I/O		Pulled-up input at reset
PC0 - PC23	Parallel IO Controller C	I/O		Pulled-up input at reset
USB Device Port				
DDM	USB Device Port Data -	Analog		
DDP	USB Device Port Data +	Analog		
USART				
SCK0 - SCK1	Serial Clock	I/O		
TXD0 - TXD1	Transmit Data	I/O		
RXD0 - RXD1	Receive Data	Input		
RTS0 - RTS1	Request To Send	Output		
CTS0 - CTS1	Clear To Send	Input		
DCD1	Data Carrier Detect	Input		
DTR1	Data Terminal Ready	Output		
DSR1	Data Set Ready	Input		
RI1	Ring Indicator	Input		
Synchronous Serial Controller				
TD	Transmit Data	Output		
RD	Receive Data	Input		
TK	Transmit Clock	I/O		
RK	Receive Clock	I/O		
TF	Transmit Frame Sync	I/O		
RF	Receive Frame Sync	I/O		
Timer/Counter				
TCLK0 - TCLK2	External Clock Inputs	Input		
TIOA0 - TIOA2	Timer Counter I/O Line A	I/O		
TIOB0 - TIOB2	Timer Counter I/O Line B	I/O		
PWM Controller				
PWM0 - PWM3	PWM Channels	Output		
Serial Peripheral Interface				
MISO	Master In Slave Out	I/O		
MOSI	Master Out Slave In	I/O		
SPCK	SPI Serial Clock	I/O		
NPCS0	SPI Peripheral Chip Select 0	I/O	Low	
NPCS1-NPCS3	SPI Peripheral Chip Select 1 to 3	Output	Low	

Table 3-1. Signal Description List (Continued)

Signal Name	Function	Type	Active Level	Comments
Two-Wire Interface				
TWD	Two-wire Serial Data	I/O		
TWCK	Two-wire Serial Clock	I/O		
Analog-to-Digital Converter				
AD0-AD3	Analog Inputs	Analog		Digital pulled-up inputs at reset
AD4-AD7	Analog Inputs	Analog		Analog Inputs
ADTRG	ADC Trigger	Input		
ADVREF	ADC Reference	Analog		
Fast Flash Programming Interface				
PGMEN0-PGMEN2	Programming Enabling	Input		
PGMM0-PGMM3	Programming Mode	Input		
PGMD0-PGMD15	Programming Data	I/O		
PGMRDY	Programming Ready	Output	High	
PGMNVALID	Data Direction	Output	Low	
PGMNOE	Programming Read	Input	Low	
PGMCK	Programming Clock	Input		
PGMNCMD	Programming Command	Input	Low	
External Bus Interface				
D[31:0]	Data Bus	I/O		
A[22:0]	Address Bus	Output		
NWAIT	External Wait Signal	Input	Low	
Static Memory Controller				
NCS[7:0]	Chip Select Lines	Output	Low	
NWR[1:0]	Write Signals	Output	Low	
NRD	Read Signal	Output	Low	
NWE	Write Enable	Output	Low	
NUB	NUB: Upper Byte Select	Output	Low	
NLB	NLB: Lower Byte Select	Output	Low	
EBI for CompactFlash Support				
CFCE[2:1]	CompactFlash Chip Enable	Output	Low	
CFOE	CompactFlash Output Enable	Output	Low	
CFWE	CompactFlash Write Enable	Output	Low	
CFIOR	CompactFlash I/O Read Signal	Output	Low	
CFIOW	CompactFlash I/O Write Signal	Output	Low	
CFRNW	CompactFlash Read Not Write Signal	Output		
CFCS[1:0]	CompactFlash Chip Select Lines	Output	Low	



Table 3-1. Signal Description List (Continued)

Signal Name	Function	Type	Active Level	Comments
EBI for NAND Flash Support				
NANDCS	NAND Flash Chip Select Line	Output	Low	
NANDOE	NAND Flash Output Enable	Output	Low	
NANDWE	NAND Flash Write Enable	Output	Low	
NANDCLE	NAND Flash Command Line Enable	Output	Low	
NANDALE	NAND Flash Address Line Enable	Output	Low	
SDRAM Controller				
SDCK	SDRAM Clock	Output		Tied low after reset
SDCKE	SDRAM Clock Enable	Output	High	
SDCS	SDRAM Controller Chip Select Line	Output	Low	
BA[1:0]	Bank Select	Output		
SDWE	SDRAM Write Enable	Output	Low	
RAS - CAS	Row and Column Signal	Output	Low	
NBS[3:0]	Byte Mask Signals	Output	Low	
SDA10	SDRAM Address 10 Line	Output		

Note: 1. Refer to [Section 6. “IO Lines Considerations”](#) on page 15.

4. Package

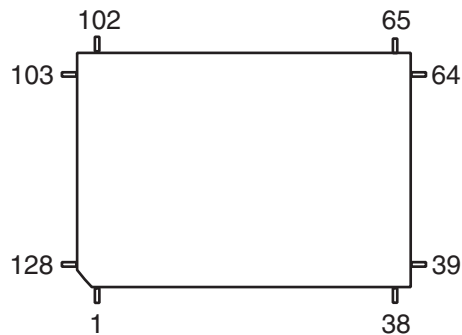
The SAM7SE512/256/32 is available in:

- 20 x 14 mm 128-lead LQFP package with a 0.5 mm lead pitch.
- 10x 10 x 1.4 mm 144-ball LFBGA package with a 0.8 mm lead pitch

4.1 128-lead LQFP Package Outline

Figure 4-1 shows the orientation of the 128-lead LQFP package and a detailed mechanical description is given in the Mechanical Characteristics section of the full datasheet.

Figure 4-1. 128-lead LQFP Package Outline (Top View)



4.2 128-lead LQFP Pinout

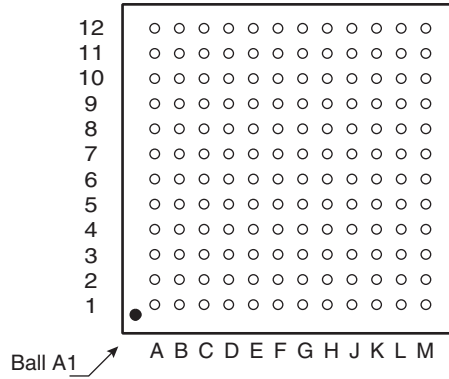
Table 4-1. Pinout in 128-lead LQFP Package

1	ADVREF	33	PB31	65	TDI	97	SDCK
2	GND	34	PB30	66	TDO	98	PC8
3	AD7	35	PB29	67	PB2	99	PC7
4	AD6	36	PB28	68	PB1	100	PC6
5	AD5	37	PB27	69	PB0	101	PC5
6	AD4	38	PB26	70	GND	102	PC4
7	VDDOUT	39	PB25	71	VDDIO	103	PC3
8	VDDIN	40	PB24	72	VDDCORE	104	PC2
9	PA20/PGMD8/AD3	41	PB23	73	NRST	105	PC1
10	PA19/PGMD7/AD2	42	PB22	74	TST	106	PC0
11	PA18/PGMD6/AD1	43	PB21	75	ERASE	107	PA31
12	PA17/PGMD5/AD0	44	PB20	76	TCK	108	PA30
13	PA16/PGMD4	45	GND	77	TMS	109	PA29
14	PA15/PGMD3	46	VDDIO	78	JTAGSEL	110	PA28
15	PA14/PGMD2	47	VDDCORE	79	PC23	111	PA27/PGMD15
16	PA13/PGMD1	48	PB19	80	PC22	112	PA26/PGMD14
17	PA12/PGMD0	49	PB18	81	PC21	113	PA25/PGMD13
18	PA11/PGMM3	50	PB17	82	PC20	114	PA24/PGMD12
19	PA10/PGMM2	51	PB16	83	PC19	115	PA23/PGMD11
20	PA9/PGMM1	52	PB15	84	PC18	116	PA22/PGMD10
21	VDDIO	53	PB14	85	PC17	117	PA21/PGMD9
22	GND	54	PB13	86	PC16	118	VDDCORE
23	VDDCORE	55	PB12	87	PC15	119	GND
24	PA8/PGMM0	56	PB11	88	PC14	120	VDDIO
25	PA7/PGMNVALID	57	PB10	89	PC13	121	DM
26	PA6/PGMNOE	58	PB9	90	PC12	122	DP
27	PA5/PGMRDY	59	PB8	91	PC11	123	VDDFLASH
28	PA4/PGMNCMD	60	PB7	92	PC10	124	GND
29	PA3	61	PB6	93	PC9	125	XIN/PGMCK
30	PA2/PGMEN2	62	PB5	94	GND	126	XOUT
31	PA1/PGMEN1	63	PB4	95	VDDIO	127	PLLRC
32	PA0/PGMEN0	64	PB3	96	VDDCORE	128	VDDPLL

4.3 144-ball LFBGA Package Outline

Figure 4-2 shows the orientation of the 144-ball LFBGA package and a detailed mechanical description is given in the Mechanical Characteristics section.

Figure 4-2. 144-ball LFBGA Package Outline (Top View)



4.4 144-ball LFBGA Pinout

Table 4-2. SAM7SE512/256/32 Pinout for 144-ball LFBGA Package

Pin	Signal Name	Pin	Signal Name	Pin	Signal Name	Pin	Signal Name
A1	PB7	D1	VDDCORE	G1	PC18	K1	PC11
A2	PB8	D2	VDDCORE	G2	PC16	K2	PC6
A3	PB9	D3	PB2	G3	PC17	K3	PC2
A4	PB12	D4	TDO	G4	PC9	K4	PC0
A5	PB13	D5	TDI	G5	VDDIO	K5	PA27/PGMD15
A6	PB16	D6	PB17	G6	GND	K6	PA26/PGMD14
A7	PB22	D7	PB26	G7	GND	K7	GND
A8	PB23	D8	PA14/PGMD2	G8	GND	K8	VDDCORE
A9	PB25	D9	PA12/PGMD0	G9	GND	K9	VDDFLASH
A10	PB29	D10	PA11/PGMM3	G10	AD4	K10	VDDIO
A11	PB30	D11	PA8/PGMM0	G11	VDDIN	K11	VDDIO
A12	PB31	D12	PA7/PGMINVALID	G12	VDDOUT	K12	PA18/PGMD6/AD1
B1	PB6	E1	PC22	H1	PC15	L1	SDCK
B2	PB3	E2	PC23	H2	PC14	L2	PC7
B3	PB4	E3	NRST	H3	PC13	L3	PC4
B4	PB10	E4	TCK	H4	VDDCORE	L4	PC1
B5	PB14	E5	ERASE	H5	VDDCORE	L5	PA29
B6	PB18	E6	TEST	H6	GND	L6	PA24/PGMD12
B7	PB20	E7	VDDCORE	H7	GND	L7	PA21/PGMD9
B8	PB24	E8	VDDCORE	H8	GND	L8	ADVREF
B9	PB28	E9	GND	H9	GND	L9	VDDFLASH
B10	PA4/PGMNCMD	E10	PA9/PGMM1	H10	PA19/PGMD7/AD2	L10	VDDFLASH
B11	PA0/PGMEN0	E11	PA10/PGMM2	H11	PA20/PGMD8/AD3	L11	PA17/PGMD5/AD0
B12	PA1/PGMEN1	E12	PA13/PGMD1	H12	VDDIO	L12	GND
C1	PB0	F1	PC21	J1	PC12	M1	PC8
C2	PB1	F2	PC20	J2	PC10	M2	PC5
C3	PB5	F3	PC19	J3	PA30	M3	PC3
C4	PB11	F4	JTAGSEL	J4	PA28	M4	PA31
C5	PB15	F5	TMS	J5	PA23/PGMD11	M5	PA25/PGMD13
C6	PB19	F6	VDDIO	J6	PA22/PGMD10	M6	DM
C7	PB21	F7	GND	J7	AD6	M7	DP
C8	PB27	F8	GND	J8	AD7	M8	GND
C9	PA6/PGMNOE	F9	GND	J9	VDDCORE	M9	XIN/PGMCK
C10	PA5/PGMRDY	F10	AD5	J10	VDDCORE	M10	XOUT
C11	PA2/PGMEN2	F11	PA15/PGMD3	J11	VDDCORE	M11	PLLRC
C12	PA3	F12	PA16/PGMD4	J12	VDDIO	M12	VDDPLL

5. Power Considerations

5.1 Power Supplies

The SAM7SE512/256/32 has six types of power supply pins and integrates a voltage regulator, allowing the device to be supplied with only one voltage. The six power supply pin types are:

- VDDIN pin. It powers the voltage regulator and the ADC; voltage ranges from 3.0V to 3.6V, 3.3V nominal.
- VDDOUT pin. It is the output of the 1.8V voltage regulator.
- VDDIO pin. It powers the I/O lines; two voltage ranges are supported:
 - from 3.0V to 3.6V, 3.3V nominal
 - or from 1.65V to 1.95V, 1.8V nominal.
- VDDFLASH pin. It powers the USB transceivers and a part of the Flash. It is required for the Flash to operate correctly; voltage ranges from 3.0V to 3.6V, 3.3V nominal.
- VDDCORE pins. They power the logic of the device; voltage ranges from 1.65V to 1.95V, 1.8V typical. It can be connected to the VDDOUT pin with decoupling capacitor. VDDCORE is required for the device, including its embedded Flash, to operate correctly.
- VDDPLL pin. It powers the oscillator and the PLL. It can be connected directly to the VDDOUT pin.

In order to decrease current consumption, if the voltage regulator and the ADC are not used, VDDIN, ADVREF, AD4, AD5, AD6 and AD7 should be connected to GND. In this case VDDOUT should be left unconnected.

No separate ground pins are provided for the different power supplies. Only GND pins are provided and should be connected as shortly as possible to the system ground plane.

5.2 Power Consumption

The SAM7SE512/256/32 has a static current of less than 60 μA on VDDCORE at 25°C, including the RC oscillator, the voltage regulator and the power-on reset when the brownout detector is deactivated. Activating the brownout detector adds 20 μA static current.

The dynamic power consumption on VDDCORE is less than 80 mA at full speed when running out of the Flash. Under the same conditions, the power consumption on VDDFLASH does not exceed 10 mA.

5.3 Voltage Regulator

The SAM7SE512/256/32 embeds a voltage regulator that is managed by the System Controller.

In Normal Mode, the voltage regulator consumes less than 100 μA static current and draws 100 mA of output current.

The voltage regulator also has a Low-power Mode. In this mode, it consumes less than 20 μA static current and draws 1 mA of output current.

Adequate output supply decoupling is mandatory for VDDOUT to reduce ripple and avoid oscillations. The best way to achieve this is to use two capacitors in parallel:

- One external 470 pF (or 1 nF) NPO capacitor should be connected between VDDOUT and GND as close to the chip as possible.

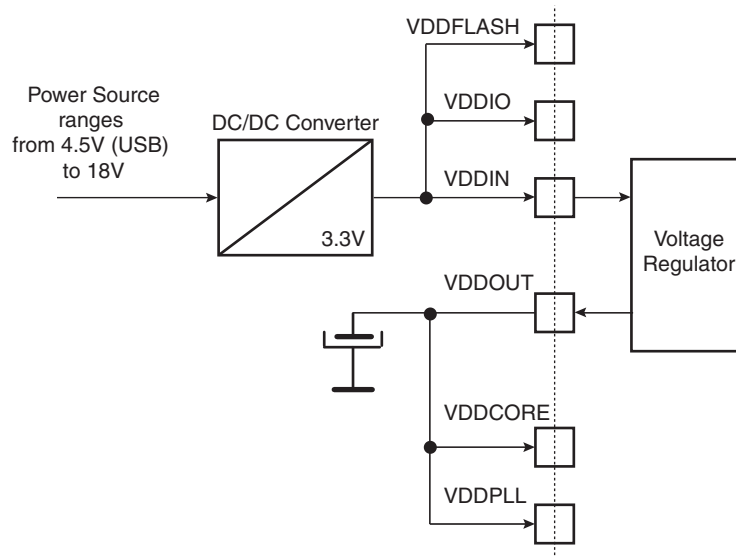
- One external 2.2 μF (or 3.3 μF) X7R capacitor should be connected between VDDOUT and GND.

Adequate input supply decoupling is mandatory for VDDIN in order to improve startup stability and reduce source voltage drop. The input decoupling capacitor should be placed close to the chip. For example, two capacitors can be used in parallel: 100 nF NPO and 4.7 μF X7R.

5.4 Typical Powering Schematics

The SAM7SE512/256/32 supports a 3.3V single supply mode. The internal regulator input connected to the 3.3V source and its output feeds VDDCORE and the VDDPLL. Figure 5-1 shows the power schematics to be used for USB bus-powered systems.

Figure 5-1. 3.3V System Single Power Supply Schematic



6. /O Lines Considerations

6.1 JTAG Port Pins

TMS, TDI and TCK are Schmitt trigger inputs. TMS, TDI and TCK do not integrate a pull-up resistor.

TDO is an output, driven at up to VDDIO, and has no pull-up resistor.

The JTAGSEL pin is used to select the JTAG boundary scan when asserted at a high level. The JTAGSEL pin integrates a permanent pull-down resistor of about 15 k Ω .

To eliminate any risk of spuriously entering the JTAG boundary scan mode due to noise on JTAGSEL, it should be tied externally to GND if boundary scan is not used, or put in place an external low value resistor (such as 1 k Ω).

6.2 Test Pin

The TST pin is used for manufacturing test or fast programming mode of the SAM7SE512/256/32 when asserted high. The TST pin integrates a permanent pull-down resistor of about 15 k Ω to GND.

To eliminate any risk of entering the test mode due to noise on the TST pin, it should be tied to GND if the FFPI is not used, or put in place an external low value resistor (such as 1 k Ω).

To enter fast programming mode, the TST pin and the PA0 and PA1 pins should be tied high and PA2 tied low.

Driving the TST pin at a high level while PA0 or PA1 is driven at 0 leads to unpredictable results.

6.3 Reset Pin

The NRST pin is bidirectional with an open-drain output buffer. It is handled by the on-chip reset controller and can be driven low to provide a reset signal to the external components or asserted low externally to reset the microcontroller. There is no constraint on the length of the reset pulse, and the reset controller can guarantee a minimum pulse length. This allows connection of a simple push-button on the NRST pin as system user reset, and the use of the NRST signal to reset all the components of the system.

An external power-on reset can drive this pin during the start-up instead of using the internal power-on reset circuit.

The NRST pin integrates a permanent pull-up of about 100 k Ω resistor to VDDIO.

This pin has Schmitt trigger input.

6.4 ERASE Pin

The ERASE pin is used to re-initialize the Flash content and some of its NVM bits. It integrates a permanent pull-down resistor of about 15 k Ω to GND.

To eliminate any risk of erasing the Flash due to noise on the ERASE pin, it should be tied externally to GND, which prevents erasing the Flash from the application, or put in place an external low value resistor (such as 1 k Ω).

This pin is debounced by the RC oscillator to improve the glitch tolerance. When the pin is tied to high during less than 100 ms, ERASE pin is not taken into account. The pin must be tied high during more than 220 ms to perform the re-initialization of the Flash.

6.5 SDCK Pin

The SDCK pin is dedicated to the SDRAM Clock and is an output-only without pull-up. Maximum Output Frequency of this pad is 48 MHz at 3.0V and 25 MHz at 1.65V with a maximum load of 30 pF.

6.6 PIO Controller lines

All the I/O lines PA0 to PA31, PB0 to PB31, PC0 to PC23 integrate a programmable pull-up resistor. Programming of this pull-up resistor is performed independently for each I/O line through the PIO controllers.

Typical pull-up value is 100 k Ω .

All the I/O lines have schmitt trigger inputs.

6.7 I/O Lines Current Drawing

The PIO lines PA0 to PA3 are high-drive current capable. Each of these I/O lines can drive up to 16 mA permanently.

The remaining I/O lines can draw only 8 mA.

However, the total current drawn by all the I/O lines cannot exceed 300 mA.

7. Processor and Architecture

7.1 ARM7TDMI Processor

- RISC processor based on ARMv4T Von Neumann architecture
 - Runs at up to 55 MHz, providing 0.9 MIPS/MHz (core supplied with 1.8V)
- Two instruction sets
 - ARM[®] high-performance 32-bit instruction set
 - Thumb[®] high code density 16-bit instruction set
- Three-stage pipeline architecture
 - Instruction Fetch (F)
 - Instruction Decode (D)
 - Execute (E)

7.2 Debug and Test Features

- EmbeddedICE[™] (Integrated embedded in-circuit emulator)
 - Two watchpoint units
 - Test access port accessible through a JTAG protocol
 - Debug communication channel
- Debug Unit
 - Two-pin UART
 - Debug communication channel interrupt handling
 - Chip ID Register
- IEEE1149.1 JTAG Boundary-scan on all digital pins

7.3 Memory Controller

- Programmable Bus Arbiter
 - Handles requests from the ARM7TDMI and the Peripheral DMA Controller
- Address decoder provides selection signals for
 - Four internal 1 Mbyte memory areas
 - One 256-Mbyte embedded peripheral area
 - Eight external 256-Mbyte memory areas
- Abort Status Registers
 - Source, Type and all parameters of the access leading to an abort are saved
 - Facilitates debug by detection of bad pointers
- Misalignment Detector
 - Alignment checking of all data accesses
 - Abort generation in case of misalignment
- Remap Command
 - Remaps the SRAM in place of the embedded non-volatile memory
 - Allows handling of dynamic exception vectors
- 16-area Memory Protection Unit (Internal Memory and peripheral protection only)

- Individually programmable size between 1K Byte and 1M Byte
- Individually programmable protection against write and/or user access
- Peripheral protection against write and/or user access
- Embedded Flash Controller
 - Embedded Flash interface, up to three programmable wait states
 - Prefetch buffer, buffering and anticipating the 16-bit requests, reducing the required wait states
 - Key-protected program, erase and lock/unlock sequencer
 - Single command for erasing, programming and locking operations
 - Interrupt generation in case of forbidden operation

7.4 External Bus Interface

- Integrates Three External Memory Controllers:
 - Static Memory Controller
 - SDRAM Controller
 - ECC Controller
- Additional Logic for NAND Flash and CompactFlash® Support
 - NAND Flash support: 8-bit as well as 16-bit devices are supported
 - CompactFlash support: all modes (Attribute Memory, Common Memory, I/O, True IDE) are supported but the signals _IOIS16 (I/O and True IDE modes) and -ATA SEL (True IDE mode) are not handled.
- Optimized External Bus:
 - 16- or 32-bit Data Bus (32-bit Data Bus for SDRAM only)
 - Up to 23-bit Address Bus, Up to 8-Mbytes Addressable
 - Up to 8 Chip Selects, each reserved to one of the eight Memory Areas
 - Optimized pin multiplexing to reduce latencies on External Memories
- Configurable Chip Select Assignment:
 - Static Memory Controller on NCS0
 - SDRAM Controller or Static Memory Controller on NCS1
 - Static Memory Controller on NCS2, Optional CompactFlash Support
 - Static Memory Controller on NCS3, NCS5 - NCS6, Optional NAND Flash Support
 - Static Memory Controller on NCS4, Optional CompactFlash Support
 - Static Memory Controller on NCS7

7.5 Static Memory Controller

- External memory mapping, 512-Mbyte address space
- 8-, or 16-bit Data Bus
- Up to 8 Chip Select Lines
- Multiple Access Modes supported
 - Byte Write or Byte Select Lines
 - Two different Read Protocols for each Memory Bank

- Multiple device adaptability
 - Compliant with LCD Module
 - Compliant with PSRAM in synchronous operations
 - Programmable Setup Time Read/Write
 - Programmable Hold Time Read/Write
- Multiple Wait State Management
 - Programmable Wait State Generation
 - External Wait Request
 - Programmable Data Float Time

7.6 SDRAM Controller

- Numerous configurations supported
 - **2K, 4K, 8K Row Address Memory Parts**
 - **SDRAM with two or four Internal Banks**
 - **SDRAM with 16- or 32-bit Data Path**
- Programming facilities
 - **Word, half-word, byte access**
 - **Automatic page break when Memory Boundary has been reached**
 - **Multibank Ping-pong Access**
 - **Timing parameters specified by software**
 - **Automatic refresh operation, refresh rate is programmable**
- **Energy-saving capabilities**
 - **Self-refresh, and Low-power Modes supported**
- Error detection
 - **Refresh Error Interrupt**
- **SDRAM Power-up Initialization by software**
- **Latency is set to two clocks (CAS Latency of 1, 3 Not Supported)**
- **Auto Precharge Command not used**
- Mobile SDRAM supported (except for low-power extended mode and deep power-down mode)

7.7 Error Corrected Code Controller

- Tracking the accesses to a NAND Flash device by triggering on the corresponding chip select
- Single bit error correction and 2-bit Random detection.
- Automatic Hamming Code Calculation while writing
 - ECC value available in a register
- Automatic Hamming Code Calculation while reading
 - Error Report, including error flag, correctable error flag and word address being detected erroneous
 - Supports 8- or 16-bit NAND Flash devices with 512-, 1024-, 2048- or 4096-byte pages

7.8 Peripheral DMA Controller

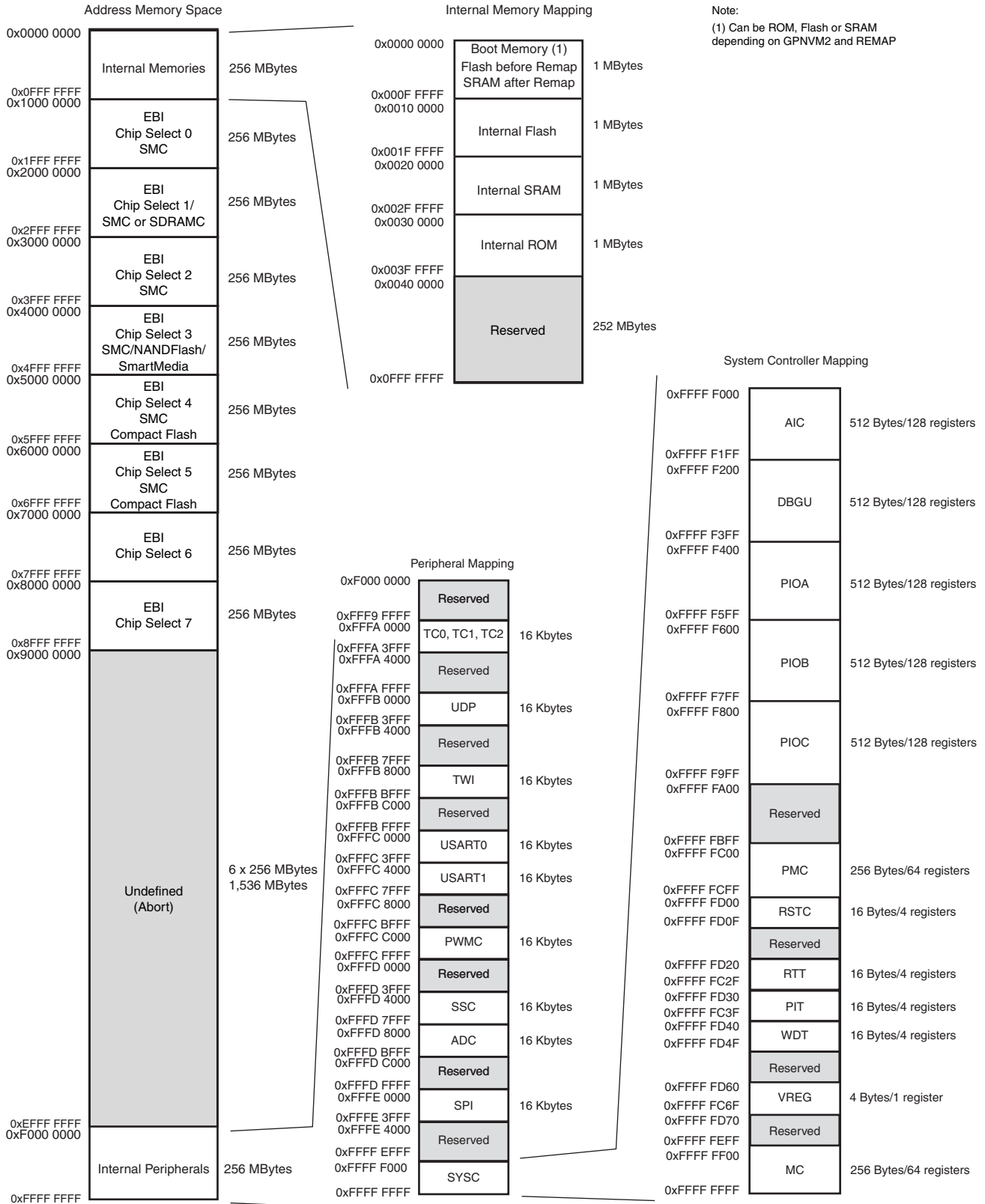
- Handles data transfer between peripherals and memories
- Eleven channels
 - Two for each USART
 - Two for the Debug Unit
 - Two for the Serial Synchronous Controller
 - Two for the Serial Peripheral Interface
 - One for the Analog-to-digital Converter
- Low bus arbitration overhead
 - One Master Clock cycle needed for a transfer from memory to peripheral
 - Two Master Clock cycles needed for a transfer from peripheral to memory
- Next Pointer management for reducing interrupt latency requirements
- Peripheral DMA Controller (PDC) priority is as follows (from the highest priority to the lowest):

Receive	DBGU
Receive	USART0
Receive	USART1
Receive	SSC
Receive	ADC
Receive	SPI
Transmit	DBGU
Transmit	USART0
Transmit	USART1
Transmit	SSC
Transmit	SPI

8. Memories

- 512 Kbytes of Flash Memory (SAM7SE512)
 - dual plane
 - two contiguous banks of 1024 pages of 256 bytes
 - Fast access time, 30 MHz single-cycle access in Worst Case conditions
 - Page programming time: 6 ms, including page auto-erase
 - Page programming without auto-erase: 3 ms
 - Full chip erase time: 15 ms
 - 10,000 write cycles, 10-year data retention capability
 - 32 lock bits, each protecting 32 lock regions of 64 pages
 - Protection Mode to secure contents of the Flash
- 256 Kbytes of Flash Memory (SAM7SE256)
 - single plane
 - one bank of 1024 pages of 256 bytes
 - Fast access time, 30 MHz single-cycle access in Worst Case conditions
 - Page programming time: 6 ms, including page auto-erase
 - Page programming without auto-erase: 3 ms
 - Full chip erase time: 15 ms
 - 10,000 cycles, 10-year data retention capability
 - 16 lock bits, each protecting 16 lock regions of 64 pages
 - Protection Mode to secure contents of the Flash
- 32 Kbytes of Flash Memory (SAM7SE32)
 - single plane
 - one bank of 256 pages of 128 bytes
 - Fast access time, 30 MHz single-cycle access in Worst Case conditions
 - Page programming time: 6 ms, including page auto-erase
 - Page programming without auto-erase: 3 ms
 - Full chip erase time: 15 ms
 - 10,000 cycles, 10-year data retention capability
 - 8 lock bits, each protecting 8 lock regions of 32 pages
 - Protection Mode to secure contents of the Flash
- 32 Kbytes of Fast SRAM (SAM7SE512/256)
 - Single-cycle access at full speed
- 8 Kbytes of Fast SRAM (SAM7SE32)
 - Single-cycle access at full speed

Figure 8-1. SAM7SE Memory Mapping



A first level of address decoding is performed by the Memory Controller, i.e., by the implementation of the Advanced System Bus (ASB) with additional features.

Decoding splits the 4G bytes of address space into 16 areas of 256M bytes. The areas 1 to 8 are directed to the EBI that associates these areas to the external chip selects NC0 to NCS7. The area 0 is reserved for the addressing of the internal memories, and a second level of decoding provides 1M byte of internal memory area. The area 15 is reserved for the peripherals and provides access to the Advanced Peripheral Bus (APB).

Other areas are unused and performing an access within them provides an abort to the master requesting such an access.

8.1 Embedded Memories

8.1.1 Internal Memories

8.1.1.1 Internal SRAM

The SAM7SE512/256 embeds a high-speed 32-Kbyte SRAM bank. The SAM7SE32 embeds a high-speed 8-Kbyte SRAM bank. After reset and until the Remap Command is performed, the SRAM is only accessible at address 0x0020 0000. After Remap, the SRAM also becomes available at address 0x0.

8.1.1.2 Internal ROM

The SAM7SE512/256/32 embeds an Internal ROM. At any time, the ROM is mapped at address 0x30 0000. The ROM contains the FFPI and the SAM-BA boot program.

8.1.1.3 Internal Flash

- The SAM7SE512 features two banks of 256 Kbytes of Flash.
- The SAM7SE256 features one bank of 256 Kbytes of Flash.
- The SAM7SE32 features one bank of 32 Kbytes of Flash.

At any time, the Flash is mapped to address 0x0010 0000.

A general purpose NVM (GPNVM) bit is used to boot either on the ROM (default) or from the Flash.

This GPNVM bit can be cleared or set respectively through the commands “Clear General-purpose NVM Bit” and “Set General-purpose NVM Bit” of the EFC User Interface.

Setting the GPNVM bit 2 selects the boot from the Flash, clearing it selects the boot from the ROM. Asserting ERASE clears the GPNVM bit 2 and thus selects the boot from the ROM by default.

Figure 8-2. Internal Memory Mapping with GPNVM Bit 2 = 0 (default)

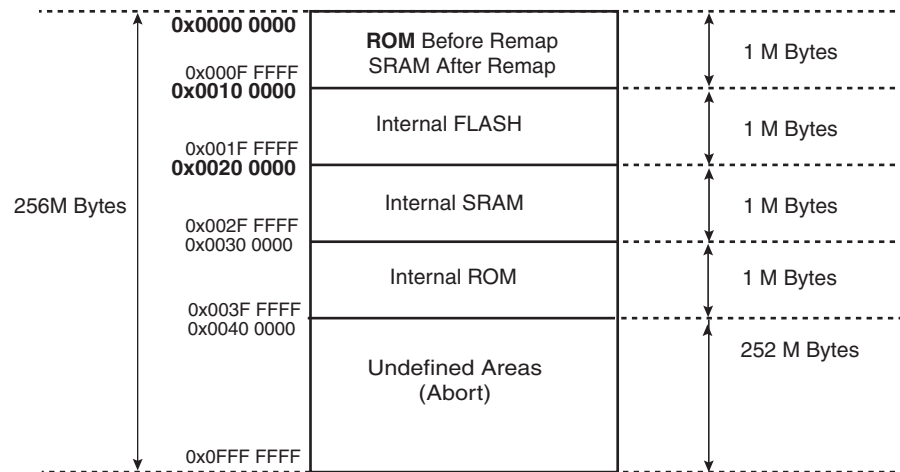
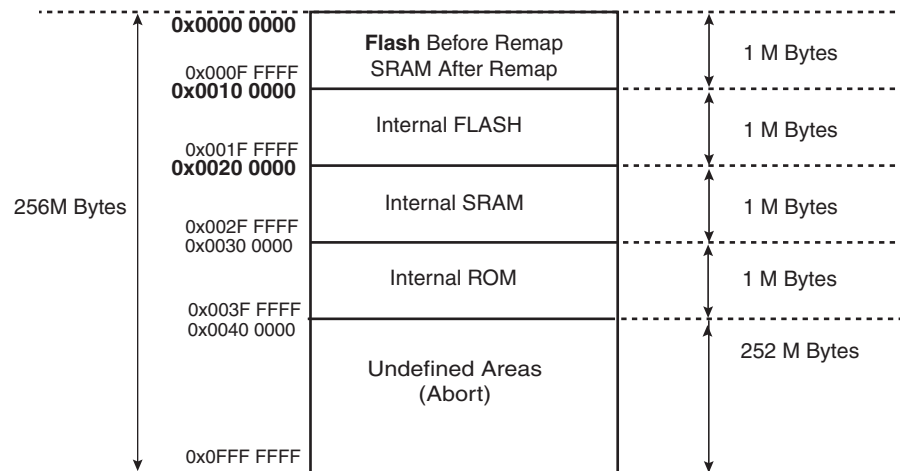


Figure 8-3. Internal Memory Mapping with GPNVM Bit 2 = 1



8.1.2 Embedded Flash

8.1.2.1 Flash Overview

The Flash of the SAM7SE512 is organized in two banks (dual plane) of 1024 pages of 256 bytes. It reads as 131,072 32-bit words.

The Flash of the SAM7SE256 is organized in 1024 pages (single plane) of 256 bytes. It reads as 65,536 32-bit words.

The Flash of the SAM7SE32 is organized in 256 pages (single plane) of 128 bytes. It reads as 8192 32-bit words.

The Flash of the SAM7SE32 contains a 128-byte write buffer, accessible through a 32-bit interface.

The Flash of the SAM7SE512/256 contains a 256-byte write buffer, accessible through a 32-bit interface.

The Flash benefits from the integration of a power reset cell and from the brownout detector. This prevents code corruption during power supply changes, even in the worst conditions.

8.1.2.2 *Embedded Flash Controller*

The Embedded Flash Controller (EFC) manages accesses performed by the masters of the system. It enables reading the Flash and writing the write buffer. It also contains a User Interface, mapped within the Memory Controller on the APB. The User Interface allows:

- programming of the access parameters of the Flash (number of wait states, timings, etc.)
- starting commands such as full erase, page erase, page program, NVM bit set, NVM bit clear, etc.
- getting the end status of the last command
- getting error status
- programming interrupts on the end of the last commands or on errors

The Embedded Flash Controller also provides a dual 32-bit Prefetch Buffer that optimizes 16-bit access to the Flash. This is particularly efficient when the processor is running in Thumb mode.

- Two EFCs (EFC0 and EFC1) are embedded in the SAM7SE512 to control each plane of 256 KBytes. Dual plane organization allows concurrent Read and Program.
- One EFC (EFC0) is embedded in the SAM7SE256 to control the single plane 256 KBytes.
- One EFC (EFC0) is embedded in the SAM7SE32 to control the single plane 32 KBytes.

8.1.2.3 *Lock Regions*

The SAM7SE512 Embedded Flash Controller manages 32 lock bits to protect 32 regions of the flash against inadvertent flash erasing or programming commands. The SAM7SE512 contains 32 lock regions and each lock region contains 64 pages of 256 bytes. Each lock region has a size of 16 Kbytes.

The SAM7SE256 Embedded Flash Controller manages 16 lock bits to protect 16 regions of the flash against inadvertent flash erasing or programming commands. The SAM7SE256 contains 16 lock regions and each lock region contains 64 pages of 256 bytes. Each lock region has a size of 16 Kbytes.

The SAM7SE32 Embedded Flash Controller manages 8 lock bits to protect 8 regions of the flash against inadvertent flash erasing or programming commands. The SAM7SE32 contains 8 lock regions and each lock region contains 32 pages of 128 bytes. Each lock region has a size of 4 Kbytes.

If a locked-region's erase or program command occurs, the command is aborted and the EFC triggers an interrupt.

The 32 (SAM7SE512), 16 (SAM7SE256) or 8 (SAM7SE32) NVM bits are software programmable through the EFC User Interface. The command "Set Lock Bit" enables the protection. The command "Clear Lock Bit" unlocks the lock region.

Asserting the ERASE pin clears the lock bits, thus unlocking the entire Flash.

8.1.2.4 *Security Bit Feature*

The SAM7SE512/256/32 features a security bit, based on a specific NVM-bit. When the security is enabled, any access to the Flash, either through the ICE interface or through the Fast Flash Programming Interface, is forbidden.